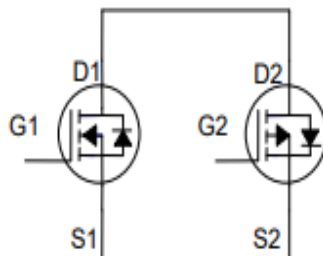


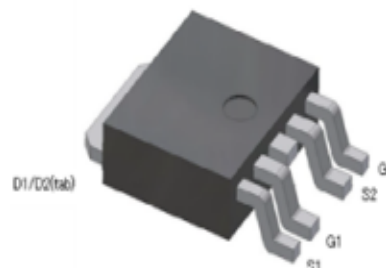


Features

- Q1: $V_{DS}=60V; I_D=16A$
- Q1: $R_{DS(ON)}=36m\Omega$ (TYP.) $V_{GS}=10V$
- Q2: $V_{DS}=-60V; I_D=-18A$
- Q2: $R_{DS(ON)}=-90m\Omega$ (TYP.) $V_{GS}=-10V$
- Reliable and Rugged
- High Current Capability
- Low On-Resistance



TO252-4L



Applications

- Load Switch
- Power management in portable/desktop PCs
- DC/DC conversion

Ordering Information

Device	package	Device Marking	Package Qty.
AP30G06GD	TO252-4	**	2500/PCS

Absolute Maximum Ratings ($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Value(Q1)	Value(Q2)	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	60	-60	V
Gate-Source Voltage ($V_{GS}=0V$, static)	V_{GS}	± 20	± 20	V
Continuous Drain Current ($T_C=25^{\circ}C$)	I_D	16	-18	A
Continuous Drain Current ($T_C=100^{\circ}C$)		10	-11	A
Single Pulsed Avalanche Energy	E_{AS}	15	21	mJ
Maximum Power Dissipation ($T_C=25^{\circ}C$)	P_D	42	42	W
Maximum Power Dissipation ($T_C=100^{\circ}C$)		20	20	W
Operating, Storage Temperature Range	T_J, T_{STG}	-55~150	-55~150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	7	-	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	63	-	$^{\circ}C/W$

Q1:Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	25	40	m Ω
		$V_{GS}=4.5V, I_D=1A$	-	33	50	
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=1A$	-	-	1.2	V

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=20V$ $V_{GS}=0V$ $f=1MHz$	-	1100	-	pF
Output capacitance	C_{oss}		-	52	-	
Reverse transfer capacitance	C_{rss}		-	45	-	
Gate Resistance	R_g	$f=1MHz$	-	3.0	-	Ω
Total Gate Charge	Q_g	$V_{DS}=20V$ $V_{GS}=10V$ $I_D=6A$	-	14	-	nC
Gate Source Charge	Q_{gs}		-	6.74	-	
Gate Drain Charge	Q_{gd}		-	1.82	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_L=3.2\Omega$ $R_G=3\Omega$	-	7.6	-	ns
Rise time	t_r		-	20	-	
Turn-off delay Time	$t_{d(off)}$		-	15	-	
Fall time	t_f		-	24	-	
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_{SD}=6A$ $dI/dt=500A/\mu s$	-	29	-	ns
Reverse Recovery Charge	Q_{rr}		-	43	-	nC

Q1:Electrical Characteristics Diagrames

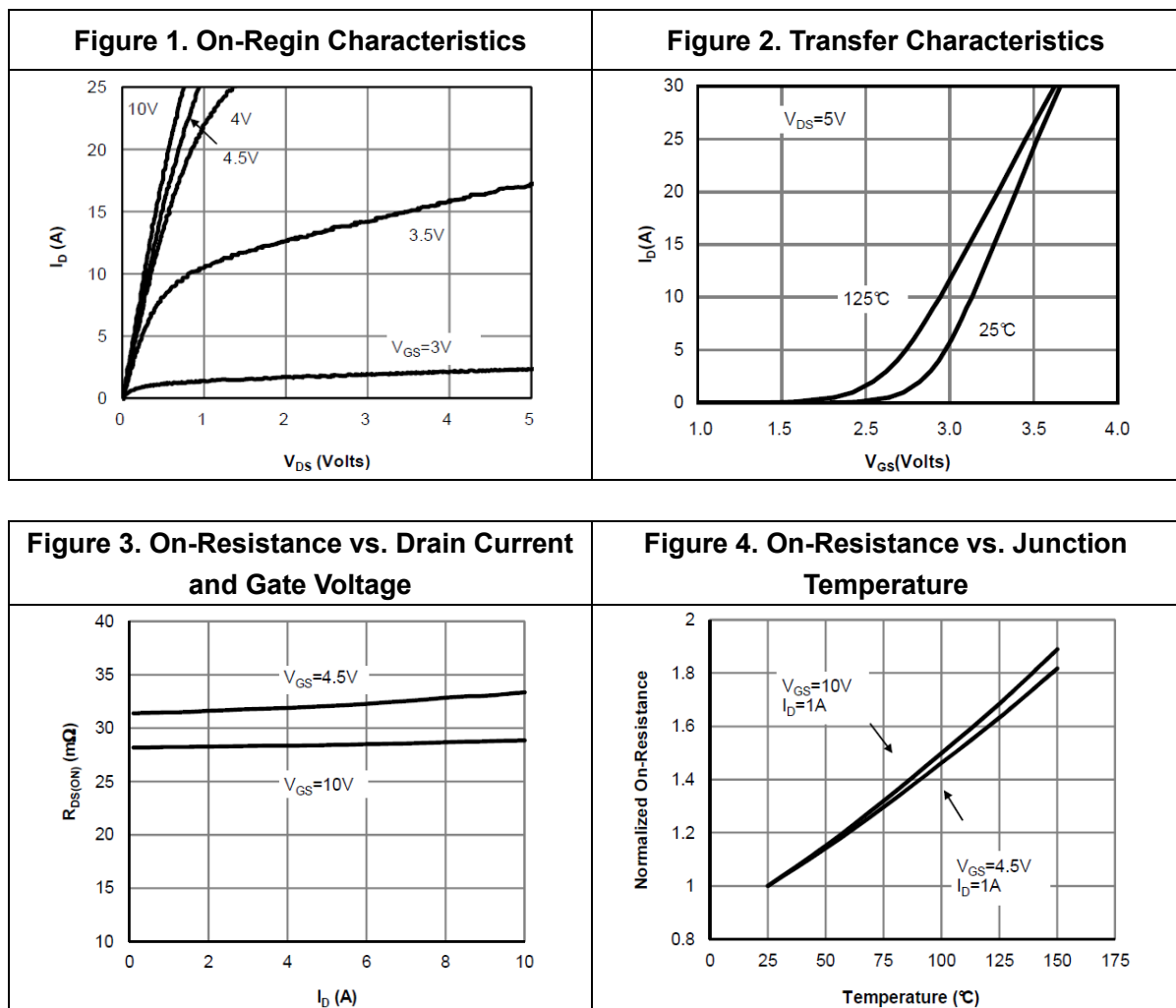


Figure 5. On-Resistance vs. Gate-Source Voltage

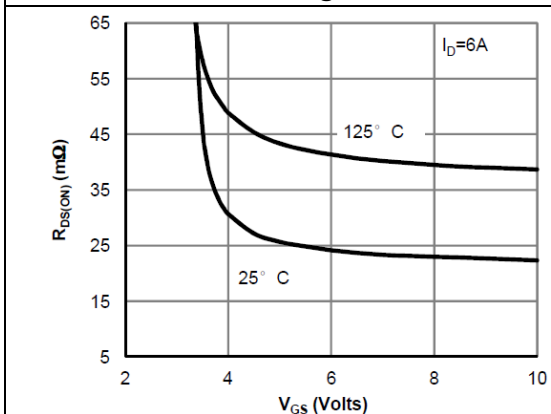


Figure 6. Body-Diode Characteristics

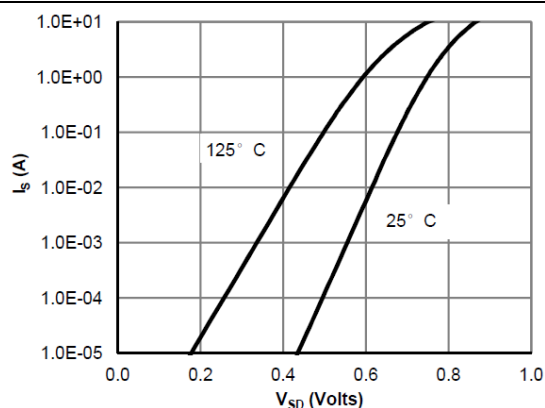


Figure 7. Gate-Charge Characteristics

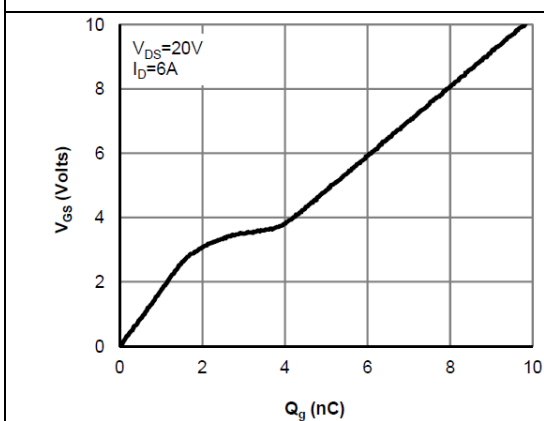


Figure 8. Capacitance Characteristics

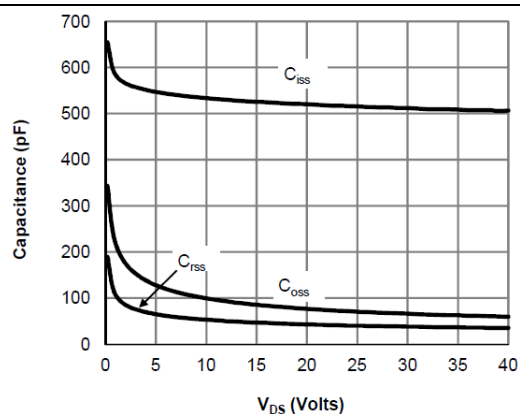


Figure 9. Maximum Forward Biased Safe Operating Area

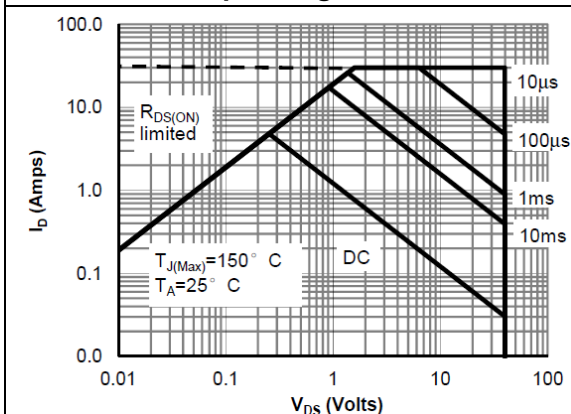


Figure 10. Single Pulse Power Rating Junction-to-Case

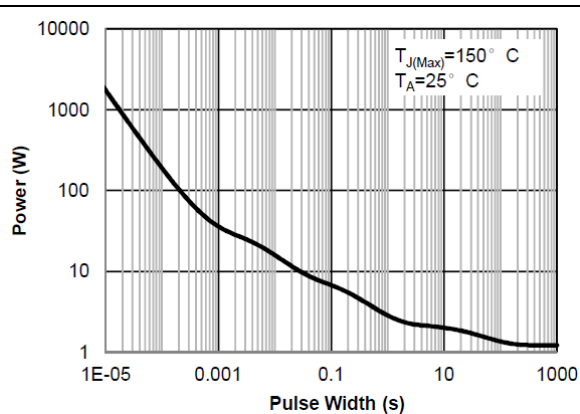
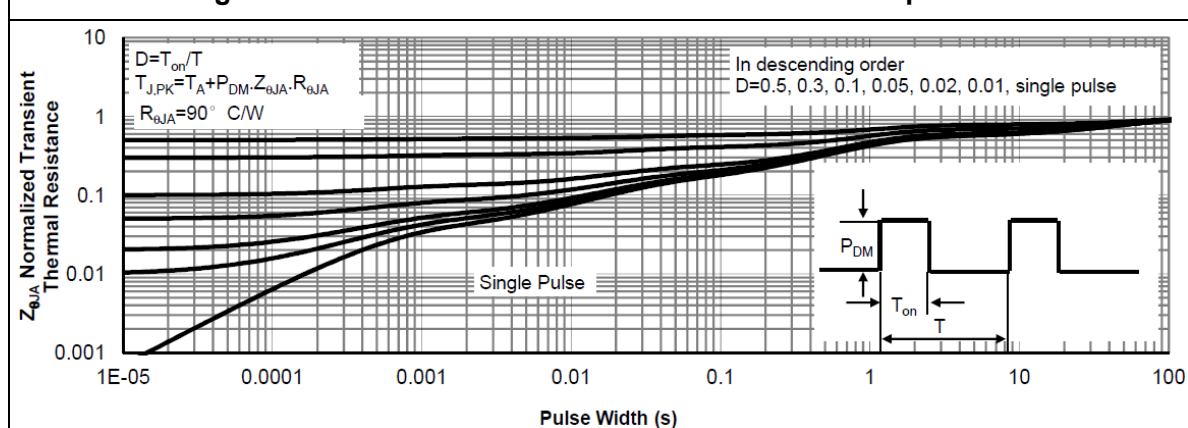


Figure 11. Normalized Maximum Transient Thermal Impedance


Q2:Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-2.2	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-1A$	-	75	90	m Ω
		$V_{GS}=-4.5V, I_D=-1A$	-	95	120	
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=-1A$	-	-	-1.2	V

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=-20V$ $V_{GS}=0V$ $f=1MHz$	-	1600	-	pF
Output capacitance	C_{oss}		-	90	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Gate Resistance	R_g	$f=1MHz$	-	8.9	-	Ω
Total Gate Charge	Q_g	$V_{DS}=-20V$ $V_{GS}=-10V$ $I_D=-5A$	-	7.5	-	nC
Gate Source Charge	Q_{gs}		-	1.65	-	
Gate Drain Charge	Q_{gd}		-	1.2	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-20V$ $R_L=4\Omega$ $R_G=3\Omega$	-	11	-	ns
Rise time	t_r		-	14	-	
Turn-off delay Time	$t_{d(off)}$		-	33	-	
Fall time	t_f		-	13	-	
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_{SD}=-5A$ $d_i/d_t=500A/\mu s$	-	35	-	ns
Reverse Recovery Charge	Q_{rr}		-	38	-	nC

Q2:Electrical Characteristics Diagrames

Figure 1. On-Regin Characteristics

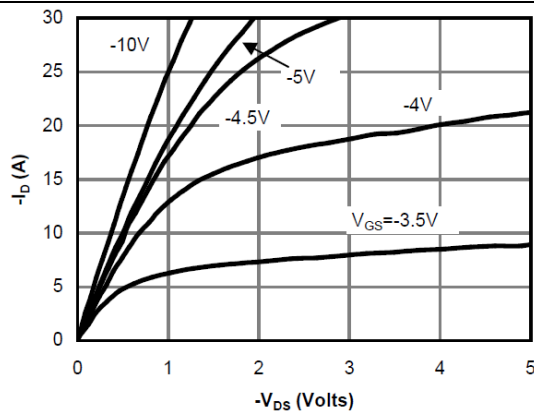


Figure 2. Transfer Characteristics

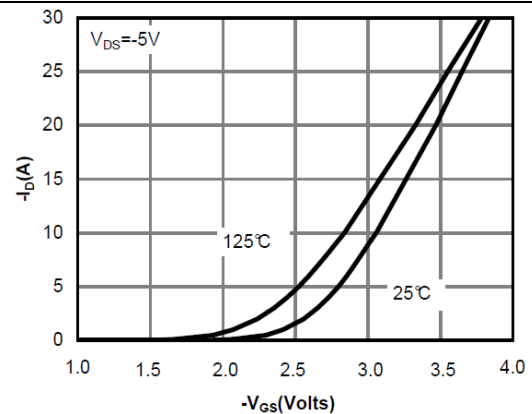


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

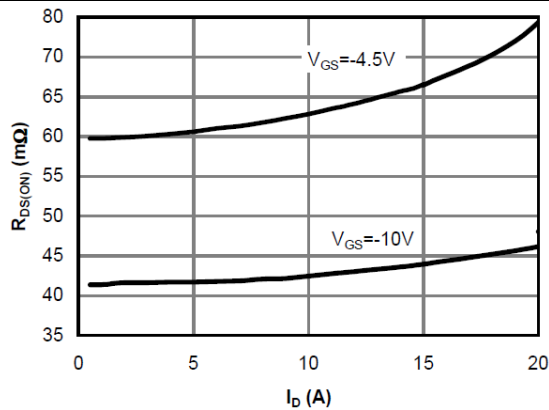


Figure 4. On-Resistance vs. Junction Temperature

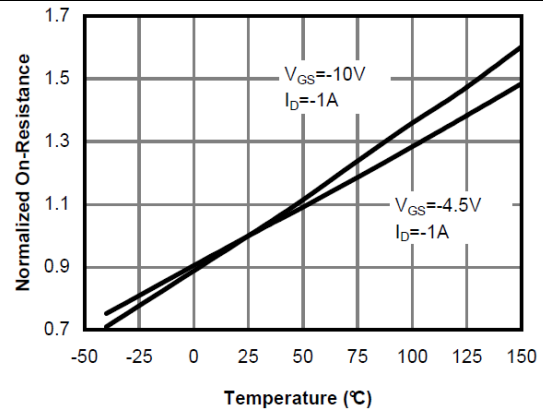


Figure 5. On-Resistance vs. Gate-Source Voltage

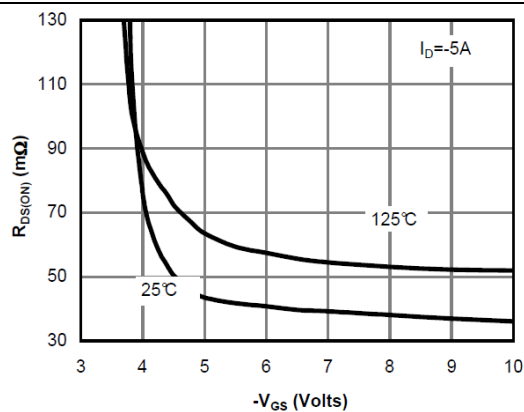


Figure 6. Body-Diode Characteristics

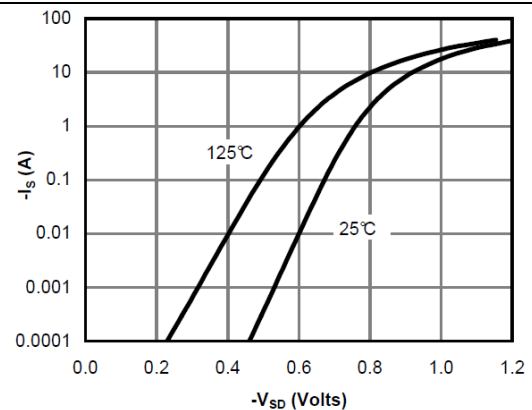


Figure 7. Gate-Charge Characteristics

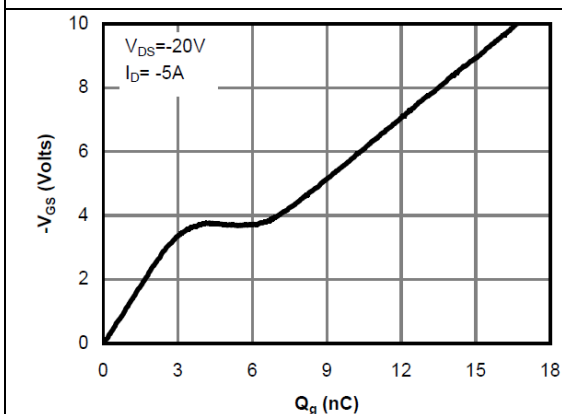


Figure 8. Capacitance Characteristics

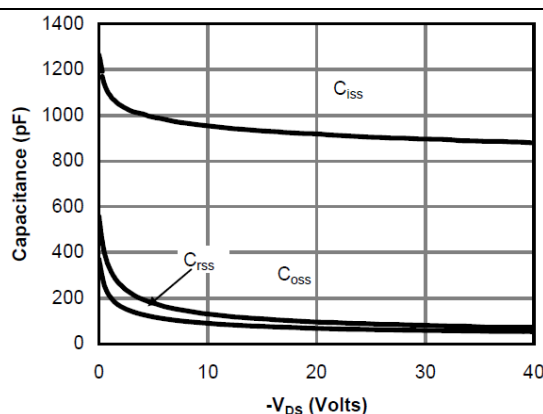


Figure 9. Maximum Forward Biased Safe Operating Area

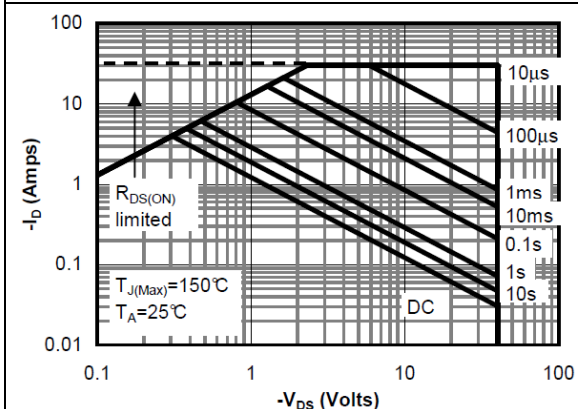


Figure 10. Single Pulse Power Rating Junction-to-Case

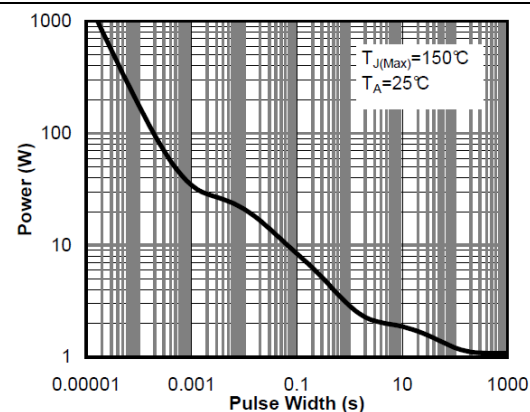
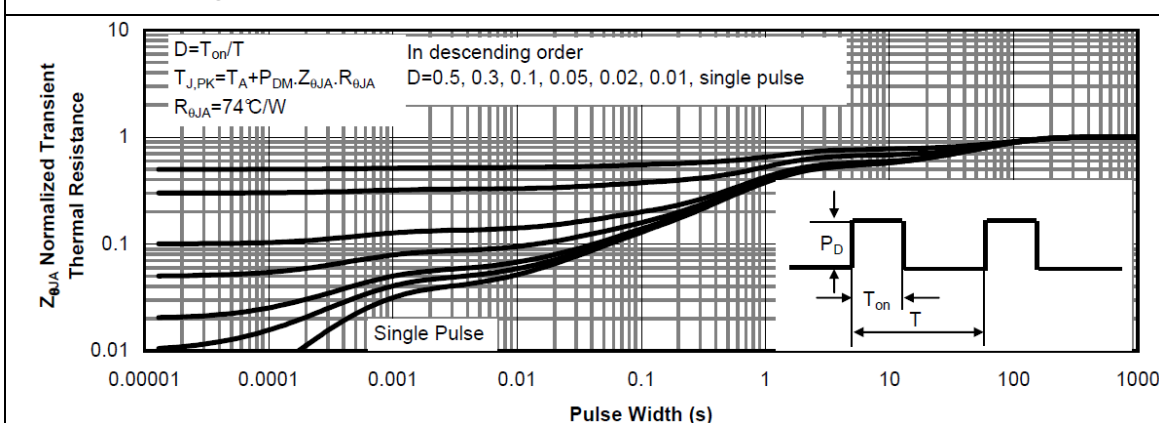


Figure 11. Normalized Maximum Transient Thermal Impedance



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